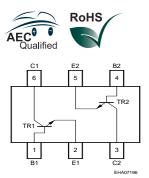


NPN Silicon RF Transistor*

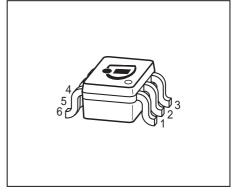
- For low noise, high-gain broadband amplifiers at collector currents from 0.5 mA to 12 mA
- $f_{\rm T}$ = 8 GHz, *F* = 0.9 dB at 900 MHz
- Two (galvanic) internal isolated Transistors in one package
- For orientation in reel see package information below
- Pb-free (RoHS compliant) package¹⁾
- Qualified according AEC Q101
- * Short term description



ESD (Electrostatic discharge) sensitive device, observe handling precaution!

| Туре | Marking | Pin Configuration | | | | | Package | |
|--------|---------|-------------------|-----|-----|-----|-----|---------|--------|
| BFS481 | RFs | 1=B | 2=E | 3=C | 4=B | 5=E | 6=C | SOT363 |

¹Pb-containing package may be available upon special request



BFS481



Maximum Ratings

| V _{CEO} | 10 | | |
|------------------|---|---|--|
| | 12 | V | |
| V _{CES} | 20 | | |
| V _{CBO} | 20 | | |
| V _{EBO} | 2 | | |
| I _C | 20 | mA | |
| I _B | 2 | | |
| P _{tot} | 175 | mW | |
| | | | |
| Ti | 150 | °C | |
| T _A | -65 150 | | |
| T _{stq} | -65 150 | | |
| | $ \begin{array}{c c} V_{CBO} \\ \hline V_{EBO} \\ \hline I_C \\ \hline I_B \\ \hline P_{tot} \\ \hline T_i \\ \hline T_A \\ \end{array} $ | V_{CBO} 20 V_{EBO} 2 I_C 20 I_B 2 P_{tot} 175 T_i 150 T_A -65 150 | |

ParameterSymbolValueUnitJunction - soldering point2) R_{thJS} \leq 380K/W

Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|---|----------------------|--------|------|------|------|
| | | min. | typ. | max. | |
| DC Characteristics | | | | | |
| Collector-emitter breakdown voltage | V _{(BR)CEO} | 12 | - | - | V |
| <i>I</i> _C = 1 mA, <i>I</i> _B = 0 | | | | | |
| Collector-emitter cutoff current | I _{CES} | - | - | 100 | μA |
| V _{CE} = 20 V, V _{BE} = 0 | | | | | |
| Collector-base cutoff current | I _{CBO} | - | - | 100 | nA |
| V _{CB} = 10 V, I _E = 0 | | | | | |
| Emitter-base cutoff current | I _{EBO} | - | - | 1 | μA |
| $V_{\rm EB}$ = 1 V, $I_{\rm C}$ = 0 | | | | | |
| DC current gain- | h _{FE} | 70 | 100 | 140 | - |
| $I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 8 V, pulse measured | | | | | |

 ${}^{1}T_{S}$ is measured on the collector lead at the soldering point to the pcb

²For calculation of $R_{\rm thJA}$ please refer to Application Note Thermal Resistance



| Parameter | Symbol | | Values | | | |
|---|---------------------------------|------|--------|------|-----|--|
| | | min. | typ. | max. | | |
| AC Characteristics (verified by random sampling) | | | | | | |
| Transition frequency | f _T | 6 | 8 | - | GHz | |
| $I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 8 V, f = 500 MHz | | | | | | |
| Collector-base capacitance | C _{cb} | - | 0.23 | 0.4 | pF | |
| $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$, | | | | | | |
| emitter grounded | | | | | | |
| Collector emitter capacitance | C _{ce} | - | 0.13 | - | | |
| $V_{CE} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$, | | | | | | |
| base grounded | | | | | | |
| Emitter-base capacitance | C _{eb} | - | 0.4 | - | | |
| $V_{\rm EB}$ = 0.5 V, f = 1 MHz, $V_{\rm CB}$ = 0 , | | | | | | |
| collector grounded | | | | | | |
| Noise figure | F | | | | dB | |
| $I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, | | | | | | |
| <i>f</i> = 900 MHz | | - | 0.9 | - | | |
| $I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, | | | | | | |
| f = 1.8 GHz | | - | 1.2 | - | | |
| Power gain, maximum stable ¹⁾ | G _{ms} | - | 20 | - | dB | |
| $I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, $Z_{\rm L}$ = $Z_{\rm Lopt}$, | | | | | | |
| <i>f</i> = 900 MHz | | | | | | |
| Power gain, maximum available ²⁾ | G _{ma} | - | 15 | - | dB | |
| $I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, $Z_{\rm L}$ = $Z_{\rm Lopt}$, | | | | | | |
| <i>f</i> = 1.8 GHz | | | | | | |
| Transducer gain | S _{21e} ² | | | | dB | |
| $I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω, | | | | | | |
| <i>f</i> = 900 MHz | | - | 16 | - | | |
| $I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω , | | | | | | |
| <i>f</i> = 1.8 MHz | | - | 11 | - | | |

Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

 ${}^{1}G_{\rm ms} = |S_{21} / S_{12}|$

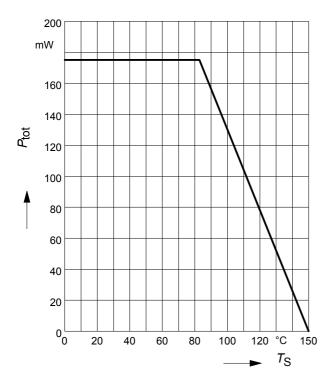
 ${}^{2}G_{\text{ma}} = |S_{21e} / S_{12e}| \ (k - (k^{2} - 1)^{1/2})$



BFS481

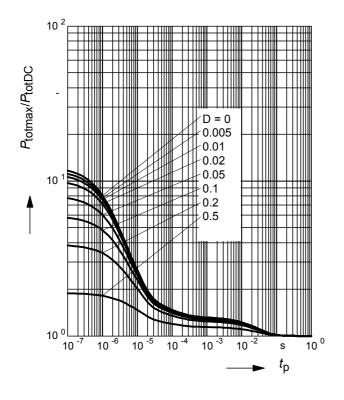
Total power dissipation $P_{tot} = f(T_S)$

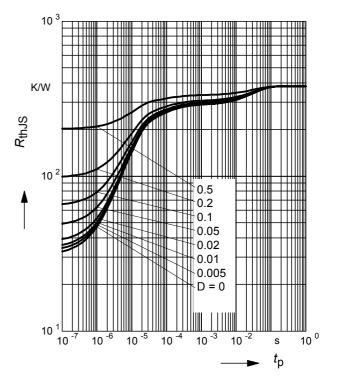
Permissible Pulse Load $R_{\text{thJS}} = f(t_p)$



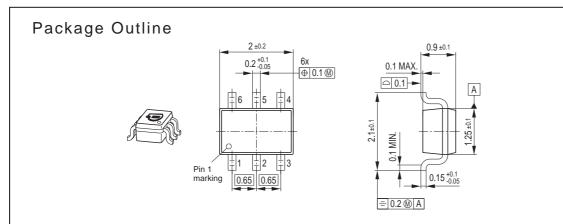
Permissible Pulse Load

 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$

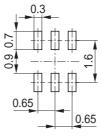






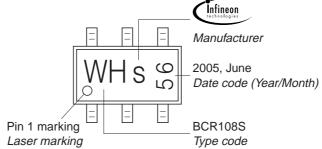


Foot Print



Marking Layout (Example)

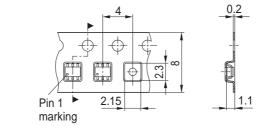
Small variations in positioning of Date code, Type code and Manufacture are possible.



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.





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